TRANSISTORS
NPN PLASTIC-ENCAPSULATE TRANSISTORS

DESCRIPTION

The devices are manufactured in planar technology with "base island" layout and monolithic Darlington configuration. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.

The TIP120_121_122 is available in TO-220-3 Package.

FEATURE

- Low collector-emitter saturation voltage
- Complementary to TIP125/126/127
- Available in TO-220-3 Package

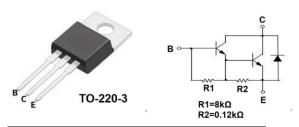
APPLICATIONS

General purpose linear and switching

ORDERING INFORMATION

Package Type	Part Number	
	TIP120	
TO-220-3	TIP121	
	TIP122	
Note	SPQ: 50pcs/Tube	
	1,000pcs/Box	
AiT provides all RoHS Compliant Products		

PIN DESCRIPTION



PIN#	DESCRIPTION
1	BASE
2	COLLECTOR
3	EMITTER

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise specified

	TIP120	60V
BV _{CBO} , Collector-Base Voltage	TIP121	80V
	TIP122	100V
BV _{CEO} , Collector-Emitter Voltage	TIP120	60V
	TIP121	80V
	TIP122	100V
BV _{EBO} , Emitter-Base Voltage		5V
Ic, Collector Current (DC)		5A
Pc, Collector Dissipation	T _A = 25°C	2W
	$T_C = 25^{\circ}C$	65W
T _{STG} , Storage Temperature		-65°C ∼ + 150°C
T _J , Junction Temperature		+150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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ELECTRICAL CHARACTERISTICS

T_A = 25°C, unless otherwise specified

Paramete	er	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-Emitter Sustaining Voltage	TIP120	VCEO(SUS)	Ic=30mA, I _B =0	60	-	-	V
	TIP121			80	-	-	
	TIP122			100	-	-	
Collector Cut-Off Current	TIP120	І _{СВО}	I _E =0, V _{CB} = 60V	-	-	0.2	mA
	TIP121		I _E =0, V _{CB} = 80V	-	-	0.2	
	TIP122		I _E =0, V _{CB} = 100V	-	-	0.2	
Collector Cut-Off Current	TIP120	Iceo	I _E =0, V _{CE} = 30V	-	-	0.5	
	TIP121		I _E =0, V _{CE} = 40V	-	-	0.5	mA
	TIP122		I _E =0, V _{CE} = 50V	-	-	0.5	
Emitter Cut-Off Curren	t	I _{EBO}	I _C =0, V _{EB} =5V	-	-	2.0	mA
DC Current Gain*		L-	I _C =0.5A, V _{CE} =3V	1000	-	-	
	h _{FE}	Ic=3A, Vce=3V	1000	-	-	_	
	V _{CE} (sat)	I _B =12mA, I _C =3A	-	-	2.0	V	
Collector-Emitter Saturation Voltage*		I _B =20mA, I _C =5A	-	-	4.0		
Base-Emitter on Voltag	je*	V _{BE(ON)}	Ic=3A, Vce=3V	-	-	2.5	V
Output Capacitance		Cob	I _E =0, V _{CB} = 10V, f=0.1MHz	-	-	200	pF

^{*}Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

Fig 1. DC Current Gain

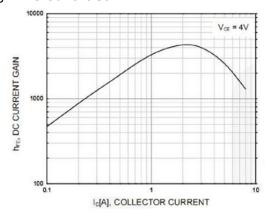


Fig 3. Base-Emitter Saturation Voltage

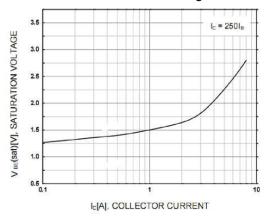


Fig 5. Safe Operating Area

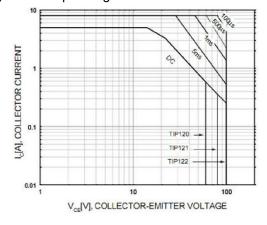


Fig 2. Collector-Emitter Saturation Voltage

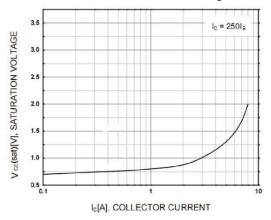


Fig 4. Output and Input Capacitance

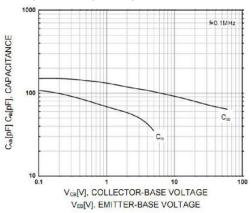
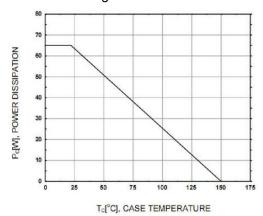


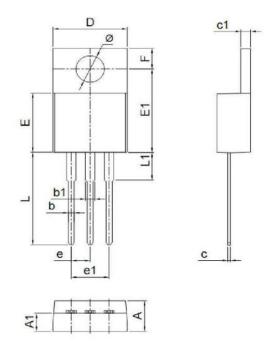
Fig 6. Power Derating



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PACKAGE INFORMATION

Dimension in TO-220-3 Package (Unit: mm)



DIM	MILLIM	ETERS		
DIM	MIN	MAX		
Α	4.300	4.700		
A1	2.520	2.820		
b	0.710	0.910		
b1	1.170	1.370		
С	0.300	0.500		
c1	1.170	1.370		
D	9.900	10.200		
Е	8.500	8.900		
E1	12.000	12.500		
е	2.440	2.640		
e1	4.880	5.280		
F	2.600	2.800		
L	13.200	13.800		
L1	3.800	4.200		
Ф	3.600	3.960		

TIP120_121_122

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